

REMARKS

Applicant thanks the Examiner for the thorough consideration given the present application. The above amendment with the following remarks is submitted to be fully responsive to the Office Action of June 29, 2000. Reconsideration in light of the amendment and the allowance of this application are respectfully requested.

Claims 23-103 stand rejected under 35 U.S.C. §112, second paragraph, as being indefinite. In addition, claims 51-57 are objected to under 37 C.F.R. §1.75(c), as being of improper dependent form. In response thereto, claims 23-29, 58, 64, 70, 76, 82, 87, 92 and 98 have been amended and claims 51-57 have been canceled to correct the deficiencies noted by the Examiner. In view thereof, withdrawal of the rejection and reconsideration is respectfully requested.

Claims 24-29 and 31-103 stand rejected under 35 U.S.C. §112, first paragraph, as containing subject matter which is not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor, at the time the application was filed, had possession of the claimed invention. In response thereto, the aforementioned amendments are believed to address the informalities noted in the Office Action and reconsideration is requested in view thereof. In addition, the Applicant respectfully traverses the rejection based upon the lack of antecedent basis in the specification for the claim limitations "amorphous film comprising silicon" or "semiconductor film comprising silicon". The Applicant respectfully contends that the recitation "amorphous film comprising silicon" may include compounds such as silicon oxide, silicon nitride or any other compound in which silicon is a necessary element. Meaning, that the types of formed film is not limited to just silicon, and may include a general semiconductor film and an insulating film as cited on pages 11-12 of the specification.

Claims 23, 25-29, 45, 47-48, 50-51, 53-57, 70-82, 84-87 and 89-103 stand rejected under 35 U.S.C. §103(a) as being unpatentable over *Kazuka* (U.S. Patent

5,420,044) in view of *Gupta et al.* (U.S. Patent 5,456,796). In response thereto, the claims have been amended to overcome the rejection and reconsideration is respectfully requested in view thereof. In particular, the rejected claims have been amended to include the method step that a discharge gas (hydrogen gas) and a reactive gas are supplied into the chamber at the same flow rate, for example at 100 SCCM. This limitation is supported in Fig. 7, thus, no issue of new matter has been presented. Applicant respectfully submits that neither over *Kazuka* nor *Gupta et al.*, alone or in combination, teaches, discloses or suggests such a method step.

In view of the foregoing, Applicant respectfully submits that the present invention is in condition for allowance and reconsideration of the pending rejections is requested in view thereof. If the Examiner deems that any further discussion would be beneficial or would expedite the prosecution of the present invention, she is invited to contact the undersigned.

Respectfully submitted,

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